

20V P-Channel Enhancement Mode MOSFET

Voltage -20 V Current -60 A

Features

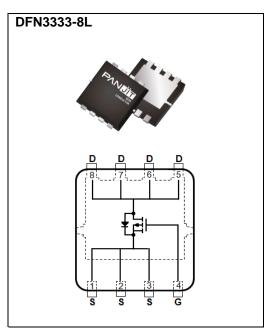
- $R_{DS(ON)}$, $V_{GS}@-4.5V$, $I_{D}@-8A<8m\Omega$
- $R_{DS(ON)}$, $V_{GS}@-2.5V$, $I_{D}@-5A<11m\Omega$
- $R_{DS(ON)}$, $V_{GS}@-1.8V$, $I_D@-3A<16m\Omega$
- Advanced Trench Process Technology.
- High density cell design for ultra-low on-resistance.
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: DFN3333-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.03 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	-20	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 12		
Continuous Drain Current	T _C =25°C	- I _D	-60	A	
	T _C =100°C		-38		
Pulsed Drain Current(Note 1,4)	T _C =25°C	I _{DM}	-200		
Power Dissipation	T _C =25°C	Po	60	10/	
	T _C =100°C		24	W	
Continuous Drain Current	T _A =25°C	I _D	-13	А	
	T _A =70°C		-10		
Power Dissipation	T _A =25°C	D	2.0	W	
Power Dissipation	T _A =70°C	Pb	1.3		
Operating Junction and Storage Temperature Range		T_{J} , T_{STG}	-55~150	°C	
Typical Thermal Resistance ^(Note 4,5)	Junction to Case	$R_{ heta JC}$	2.1	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		

Limited only By Maximum Junction Temperature



Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =-250uA	uA -20 -		-	V	
Gate Threshold Voltage	$V_{GS(th)}$	V _{DS} =V _{GS} ,I _D =-250uA	-0.3	-0.6	-1.0	V	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-4.5V,I _D =-8A	-	6	8		
		V _{GS} =-2.5V,I _D =-5A -		8	11	mΩ	
		V _{GS} =-1.8V,I _D =-3A	-	11	16]	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-20V,V _{GS} =0V	-	-	-1.0	uA	
Gate-Source Leakage Current	Igss	V _{GS} = <u>+</u> 12V,V _{DS} =0V	-	-	<u>+</u> 100	nA	
Dynamic ^(Note 6)							
Total Gate Charge	Q_g	\/ 40\/ I 5A	-	46.8	-	nC	
Gate-Source Charge	Q_gs	V _{DS} =-10V, I _D =-5A, V _{GS} =-4.5V ^(Note 1,2)	-	7.4	-		
Gate-Drain Charge	Q_gd	VGS=-4.5 V(Note 1,2)	-	11.1	-		
Input Capacitance	Ciss	\/ 45\/ \/ 0\/	-	4659	-	pF	
Output Capacitance	Coss	V _{DS} =-15V, V _{GS} =0V,	-	539	-		
Reverse Transfer Capacitance	Crss	f=1.0MHZ	-	440	-		
Turn-On Delay Time	td _(on)	\/ 40\/ ID 44	-	42	-	ns	
Turn-On Rise Time	t _r	V _{DS} =-10V,ID=-1A,	-	78	-		
Turn-Off Delay Time	td _(off)	V _{GS} =-4.5V, R _G =25Ω	-	510	-		
Turn-Off Fall Time	t _f	(1000 1,2)	-	265	-		
Drain-Source Diode							
Maximum Continuous Drain-Source Diode Forward Current	Is		-	-	-60	А	
Diode Forward Voltage	V _{SD}	Is=-1A,V _{GS} =0V	-	-0.7	-1	V	

NOTES:

- 1. Pulse width < 300us, Duty cycle < 2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.



TYPICAL CHARACTERISTIC CURVES

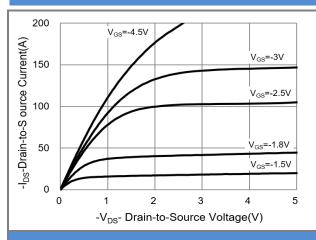


Fig.1 On-Region Characteristics

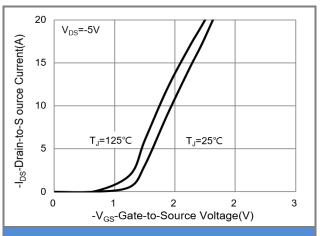


Fig.2 Transfer Characteristics

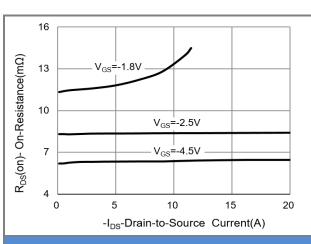


Fig.3 On-Resistance vs. Drain Current

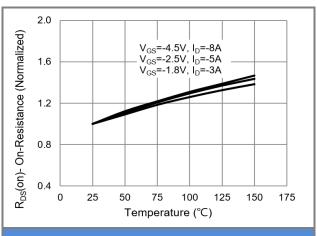


Fig.4 On-Resistance vs. Junction temperature

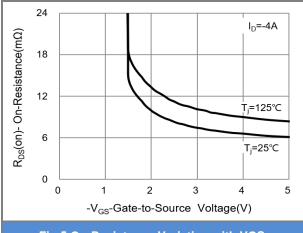


Fig.5 On-Resistance Variation with VGS.

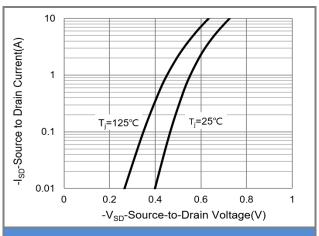


Fig.6 Source-Drain Diode Forward Voltage



TYPICAL CHARACTERISTIC CURVES

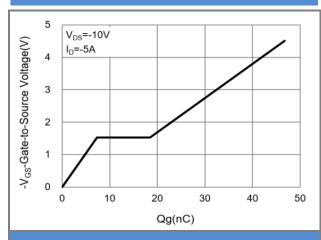


Fig.7 Gate-Charge Characteristics

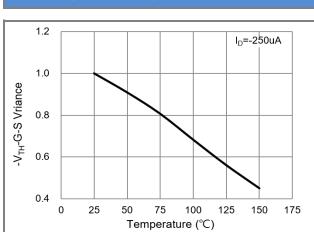
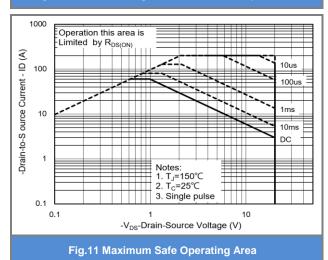


Fig.9 Threshold Voltage Variation with Temperature



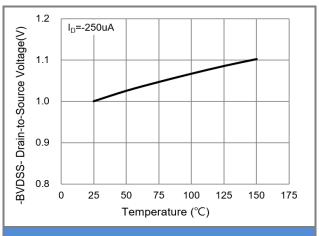


Fig.8 Breakdown Voltage Variation vs. Temperature.

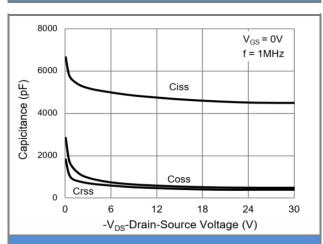


Fig.10 Capacitance vs. Drain-Source Voltage



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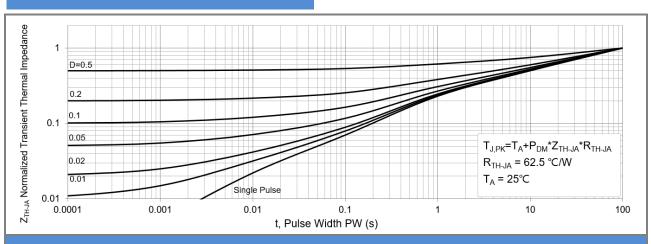


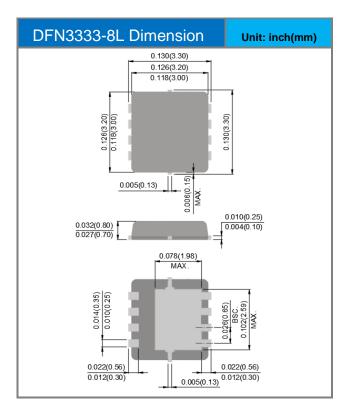
Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

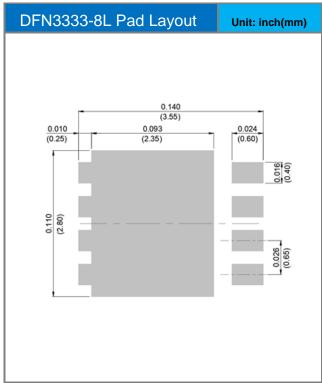


Product and Packing Information

Part No.	Package Type	Packing Type	Marking	
PJQ4411P	DFN3333-8L	5K pcs / 13" reel	4411	

Packaging Information & Mounting Pad Layout







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